

MA3U755

Silicon epitaxial planar type (cathode common)

For switching power supply

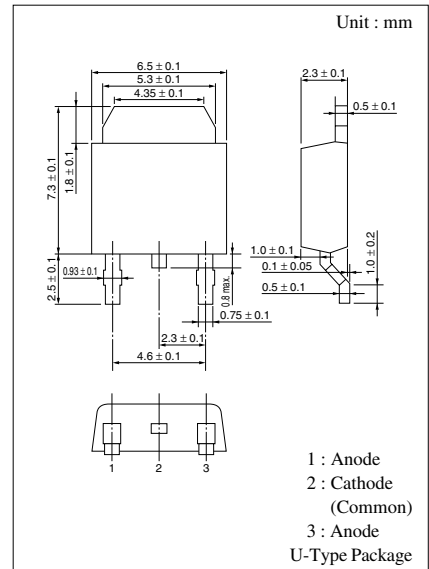
■ Features

- Small U-type package and allowing surface mounting
- Low forward rise voltage V_F
- Cathode common dual type

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	60	V
Average forward current	$I_{F(AV)}$	5	A
Non-repetitive peak forward surge current*	I_{FSM}	40	A
Junction temperature	T_j	-40 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

Note) * : Half sine-wave; 10 ms/cycle



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 60\text{ V}, T_C = 25^\circ\text{C}$			1.0	mA
Forward voltage (DC)	V_F	$I_F = 2.5\text{ A}, T_C = 25^\circ\text{C}$			0.58	V
Thermal resistance*	$R_{th(j-c)}$	Between junction and case			12.5	$^\circ\text{C}/\text{W}$

Note) Rated input/output frequency: 1 000 MHz

* : $T_C = 25^\circ\text{C}$

